

10-BIT 1.25-MSPS MICRO-POWER MINIATURE SAR ANALOG-TO-DIGITAL CONVERTER

Check for Samples: ADS7887M

FEATURES

- 1.25-MHz Sample Rate Serial Device
- 10-Bit Resolution
- Zero Latency
- 25-MHz Serial Interface
- Supply Range: 2.35 V to 5.25 V
- Typical Power Dissipation at 1.25 MSPS:
 - 3.8 mW at 3-V V_{DD}
 - 8 mW at 5-V V_{DD}
- ±0.35 LSB INL, DNL
- 61-dB SINAD, -84-dB THD
- Unipolar Input Range: 0 V to V_{DD}
- Power Down Current: 10 µA Max
- Wide Input Bandwidth: 15 MHz at 3 dB
- 6-Pin SOT23 Package

APPLICATIONS

- Base Band Converters in Radio
 Communication
- Motor Current/Bus Voltage Sensors in Digital Drives
- Optical Networking (DWDM, MEMS Based Switching)
- Optical Sensors
- Battery Powered Systems
- Medical Instrumentations
- High-Speed Data Acquisition Systems
- High-Speed Closed-Loop Systems

DESCRIPTION

The ADS7887 is a 10-bit 1.25-MSPS analog-to-digital converter (ADC). The device includes a capacitor-based SAR A/D converter with inherent sample and hold. The serial interface is controlled by the CS and SCLK signals for glueless connections with microprocessors and DSPs. The input signal is sampled with the falling edge of CS, and SCLK is used for conversion and serial data output.

The device operates from a wide supply range from 2.35 V to 5.25 V. The low power consumption of the device makes it suitable for battery-powered applications. The device also includes a power-saving powerdown feature for when the device is operated at lower conversion speeds.

The high level of the digital input to the device is not limited to device V_{DD} . This means the digital input can go as high as 5.25 V when device supply is 2.35 V. This feature is useful when digital signals are coming from other circuits with different supply levels. Also, this relaxes restriction on power-up sequencing.

The ADS7887 is available in a 6-pin SOT23 package and is specified for operation from -55°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

ADS7887M



SLAS750A - JUNE 2011 - REVISED JUNE 2011

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

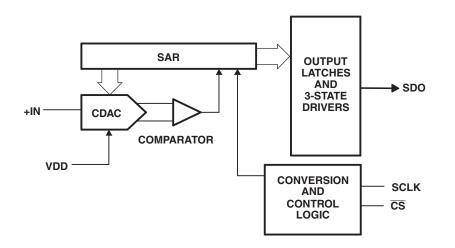
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION⁽¹⁾

ſ	T _A	PACK	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	–55°C to 125°C	SOT-23 – DBV	Reel of 250	ADS7887MDBVT	BCNM

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

+IN to AGND		–0.3 V to +V _{DD} +0.3 V		
+V _{DD} to AGND		–0.3 V to 7.0 V		
Digital input voltage to GND		–0.3V to (7.0 V)		
Digital output to GND		–0.3 V to (+V _{DD} + 0.3 V)		
Operating temperature range		–55°C to 125°C		
Storage temperature range		–65°C to 150°C		
Junction temperature (T _J Max)		150°C		
Power dissipation		$(T_J Max - T_A)/\theta_{JA}$		
θ_{JA} Thermal impedance ⁽²⁾		295.2°C/W		
	Vapor phase (60 sec)	215°C		
Lead temperature, soldering	Infrared (15 sec)	220°C		

(1) Stresses above those listed under *absolute maximum ratings* may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods may affect device reliability.

(2) The package thermal impedance is calculated in accordance with JESD 51-7, except for through-hole packages, which use a trace length of zero.



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ELECTRICAL SPECIFICATIONS

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALO	G INPUT					
	Full-scale input voltage span ⁽¹⁾		0		V _{DD}	V
	Absolute input voltage range	+IN	-0.20		V _{DD} +0.20	V
C _i	Input capacitance ⁽²⁾			21		pF
l _{likg}	Input leakage current	$T_A = 125^{\circ}C$		40		nA
SYSTEM	M PERFORMANCE					
	Resolution			10		Bits
	No missing codes		10			Bits
INL	Integral nonlinearity		-1.2	±0.35	1.2	LSB ⁽³⁾
DNL	Differential nonlinearity		-1 ⁽⁴⁾	±0.35	1.35	LSB
Eo	Offset error ⁽⁵⁾ (6) (7)		-2.5	±0.5	2.5	LSB
E _G	Gain error ⁽⁶⁾		-2	±0.5	2	LSB
SAMPL	ING DYNAMICS					
	Conversion time	25-MHz SCLK	530	560		ns
	Acquisition time		260			ns
	Maximum throughput rate	25-MHz SCLK			1.25	MHz
	Aperture delay			5		ns
	Step response			160		ns
	Overvoltage recovery			160		ns
DYNAM	IC CHARACTERISTICS					
THD	Total harmonic distortion ⁽⁸⁾	100 kHz		-84	-67	dB
SINAD	Signal-to-noise and distortion	100 kHz	59	61		dB
SFDR	Spurious free dynamic range	100 kHz	70	81		dB
	Full power bandwidth	At –3 dB		15		MHz
DIGITAI	L INPUT/OUTPUT					
Logic fa	mily — CMOS					
V _{IH}	High-level input voltage	VDD = 2.35 V to 5.25 V	V _{DD} – 0.4		5.25	V
	Level and the set of the set	$V_{DD} = 5 V$			0.8	
VIL	Low-level input voltage	$V_{DD} = 3 V$			0.4	V
V _{он}	High-level output voltage	At I _{source} = 200 μA	V _{DD} -0.2			
V _{OL}	Low-level output voltage	At I _{sink} = 200 μA			0.4	V
POWER	SUPPLY REQUIREMENTS				,	
+V _{DD}	Supply voltage		2.35	3.3	5.25	V
		At V_{DD} = 2.35 V to 5.25 V, 1.25-MHz throughput			2	
	Supply current (normal mode)	At V _{DD} = 2.35 V to 5.25 V, static state			1.5	mA
		SCLK off			10	
	Power-down state supply current	SCLK on (25 MHz)			200	μA
	Power dissipation at 1.25 MHz	V _{DD} = 5 V		8	10	
	throughput	$V_{DD} = 3 V$		3.8	6	mW

Ideal input span; does not include gain or offset error. Refer Figure 21 for details on sampling circuit LSB means least significant bit (1)

(2) (3)

(4) Exclusive

Measured relative to an ideal full-scale input (5)

Offset error and gain error ensured by characterization. First transition of 000H to 001H at 0.5 × $(V_{ref}/2^{10})$ (6)

(7)

(8) Calculated on the first nine harmonics of the input frequency

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STRUMENTS

EXAS

ELECTRICAL SPECIFICATIONS (continued)

+V_{DD} = 2.35 V to 5.25 V, T_A = –55°C to 125°C, f_{sample} = 1.25 MHz

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Dower discipation in static state	$V_{DD} = 5 V$		5.5	7.5	mW
Power dissipation in static state	V _{DD} = 3 V		3	4.5	mvv
Power down time				0.1	μs
Power up time				0.8	μs
Invalid conversions after power up				1	
TEMPERATURE RANGE					
Specified performance		-55		125	°C

TIMING REQUIREMENTS (see Figure 1)

All specifications typical at $T_A = -55^{\circ}C$ to $125^{\circ}C$, $V_{DD} = 2.35$ V to 5.25 V, unless otherwise specified.

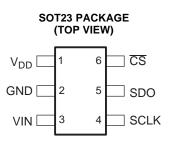
	PARAMETER	TEST CONDITIONS ⁽¹⁾	MIN	TYP	MAX	UNIT			
	Conversion time	$V_{DD} = 3 V$			14 × t _{SCLK}				
t _{conv}	Conversion time	V _{DD} = 5 V			14 × t _{SCLK}	ns			
	Minimum quiet time needed from bus 3-state to start of	$V_{DD} = 3 V$	40						
tq	next conversion	V _{DD} = 5 V	40			ns			
		$V_{DD} = 3 V$		15	25	ns			
t _{d1}	Delay time, \overline{CS} low to first data (0) out	V _{DD} = 5 V		13	25	ns			
	Setup time, CS low to SCLK low	$V_{DD} = 3 V$	10			25 			
t _{su1}	Setup time, CS low to SCLK low	$V_{DD} = 5 V$	10			ns			
		$V_{DD} = 3 V$		15	25	ne			
t _{d2}	Delay time, SCLK falling to SDO	$V_{DD} = 5 V$		13	25	ns			
		V _{DD} < 3 V	7						
t _{h1}	Hold time, SCLK falling to data valid ⁽²⁾	V _{DD} > 5 V	5.5			ns			
	Delautine 40th COLIX felling edge to CDO 2 state	V _{DD} = 3 V		10	25				
t _{d3}	Delay time, 16th SCLK falling edge to SDO 3-state	$V_{DD} = 5 V$		8	20	ns			
	Data duration 70	$V_{DD} = 3 V$	25	40		2			
t _{w1}	Pulse duration, \overline{CS}	V _{DD} = 5 V	25	40		ns			
		$V_{DD} = 3 V$		17	30				
t _{d4}	Delay time, \overline{CS} high to SDO 3-state	$V_{DD} = 5 V$		15	25	ns			
	Dulas duration COLIC high	$V_{DD} = 3 V$ 0.4 × t _{SCLK}				ns			
t _{wH}	Pulse duration, SCLK high	$V_{DD} = 5 V$	0.4 × t _{SCLK}						
	Dulas duration COLIC Inv	$V_{DD} = 3 V$	0.4 × t _{SCLK}						
t _{wL}	Pulse duration, SCLK low	$V_{DD} = 5 V$	0.4 × t _{SCLK}			ns			
		$V_{DD} = 3 V$			25				
	Frequency, SCLK	$V_{DD} = 5 V$			25	MHz			
	Delay time, second falling edge of clock and \overline{CS} to	$V_{DD} = 3 V$	-2		5				
t _{d5}	enter in powerdown (use minimum specification to avoid accidently entering powerdown) Figure 2	V _{DD} = 5 V	-2		5	ns 5			
	Delay time, \overline{CS} and 10th falling edge of clock to enter in	$V_{DD} = 3 V$	2		-5				
t _{d6}	powerdown (use maximum specification to avoid accidently entering powerdown) Figure 2	$V_{DD} = 5 V$	2		-5	ns			

(1) 3-V Specifications apply from 2.35 V to 3.6 V, and 5-V specifications apply from 4.75 V to 5.25 V.

(2) With 50-pf load.

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DEVICE INFORMATION



TERMINAL FUNCTIONS

TER	TERMINAL		RMINAL I/O		DESCRIPTION
NAME	NO.	1/0	DESCRIPTION		
V _{DD}	1	_	Power supply input also acts like a reference voltage to ADC.		
GND	2	-	Ground for power supply, all analog and digital signals are referred with respect to this pin.		
VIN	3	I	Analog signal input		
SCLK	4	I	Serial clock		
SDO	5	0	Serial data out		
CS	6	I	Chip select signal, active low		

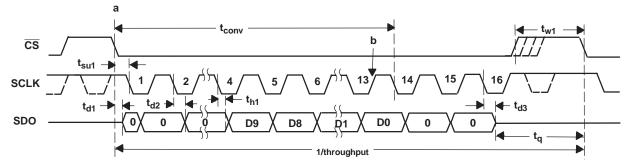
NORMAL OPERATION

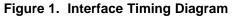
The cycle begins with the falling edge of \overline{CS} . This point is indicated as **a** in Figure 1. With the falling edge of \overline{CS} , the input signal is sampled and the conversion process is initiated. The device outputs data while the conversion is in progress. The data word contains 4 leading zeros, followed by 10-bit data in MSB first format and padded by 2 lagging zeros.

The falling edge of \overline{CS} clocks out the first zero, and a zero is clocked out on every falling edge of the clock until the third edge. Data is in MSB first format with the MSB being clocked out on the 4th falling edge. Data is padded with two lagging zeros as shown in Figure 1. On the 16th falling edge of SCLK, SDO goes to the 3-state condition. The conversion ends on the 14th falling edge of SCLK. The device enters the acquisition phase on the first rising edge of SCLK after the 13th falling edge. This point is indicated by **b** in Figure 1.

 \overline{CS} can be asserted (pulled high) after 16 clocks have elapsed. Do not start the next conversion by pulling \overline{CS} low until the end of the quiet time (t_q) after SDO goes to 3-state. To continue normal operation, do not pull \overline{CS} high until point **b**. Without this, the device does not enter the acquisition phase and no valid data is available in the next cycle. (Also refer to power down mode for more details.) \overline{CS} going high any time after the conversion start aborts the ongoing conversion and SDO goes to 3-state.

The high level of the digital input to the device is not limited to device V_{DD} . This means the digital input can go as high as 5.25 V when the device supply is 2.35 V. This feature is useful when digital signals are coming from another circuit with different supply levels. Also, this relaxes the restriction on power up sequencing. However, the digital output levels (V_{OH} and V_{OL}) are governed by V_{DD} as listed in the SPECIFICATIONS table.





SLAS750A - JUNE 2011 - REVISED JUNE 2011

POWER-DOWN MODE

The device enters power down mode if \overline{CS} goes high anytime after the second SCLK falling edge to before the tenth SCLK falling edge. Ongoing conversion stops and SDO goes to 3-state under this power-down condition as shown in Figure 2.

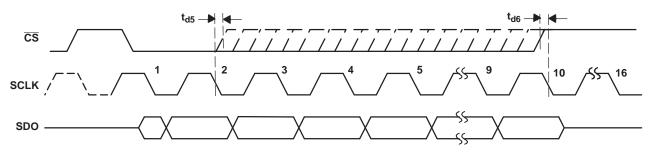


Figure 2. Entering Power Down Mode

A dummy cycle with \overline{CS} low for more than ten SCLK falling edges brings the device out of power-down mode. For the device to come to the fully powered up condition it takes 0.8 µs. \overline{CS} can be pulled high any time after the 10th falling edge as shown in Figure 3. It is not necessary to continue until the 16th clock if the next conversion starts 0.8 µs after \overline{CS} going low of the dummy cycle and the quiet time (t_q) condition is met.

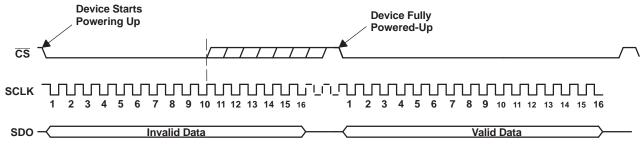
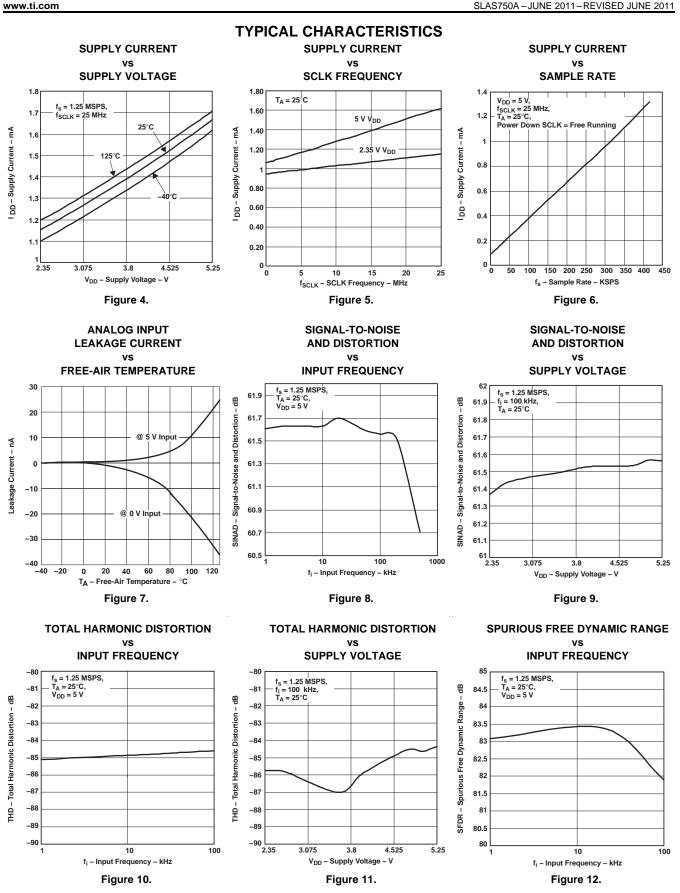


Figure 3. Exiting Power Down Mode





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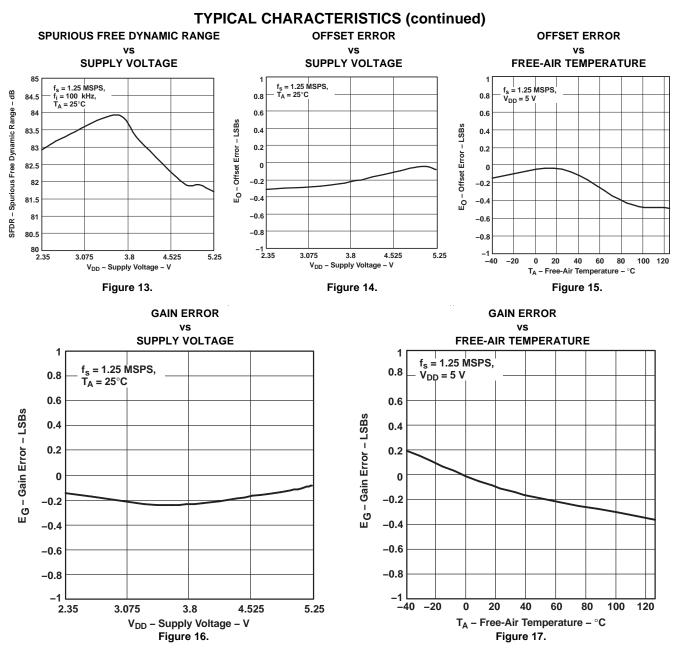
Product Folder Link(s): ADS7887M

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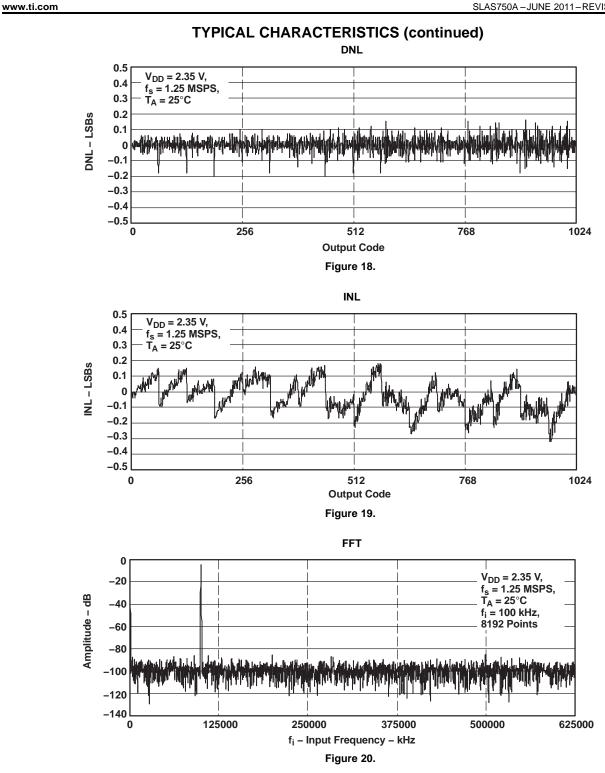
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SLAS750A - JUNE 2011 - REVISED JUNE 2011

APPLICATION INFORMATION

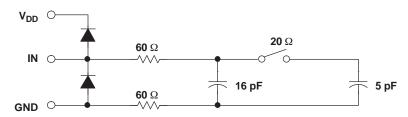


Figure 21. Typical Equivalent Sampling Circuit

Driving the VIN and V_{DD} Pins

The VIN input to the ADS7887 should be driven with a low-impedance source. In most cases, additional buffers are not required. In cases where the source impedance exceeds 200 Ω , using a buffer helps achieve the rated performance of the converter. The THS4031 is a good choice for the driver amplifier buffer.

The reference voltage for the ADS7887 A/D converter is derived internally from the supply voltage. The device offer limited low-pass filtering functionality on-chip. The supply to the converter should be driven with a low-impedance source and should be decoupled to ground. A 1- μ F storage capacitor and a 10-nF decoupling capacitor should be placed close to the device. Wide low-impedance traces should be used to connect the capacitor to the pins of the device. The ADS7887 draws very little current from the supply lines. The supply line can be driven:

- Directly from the system supply.
- From a reference output from a low-drift and low-dropout reference voltage generator like REF3030 or REF3130. The ADS7887 can operate off a wide range of supply voltages. The actual choice of the reference voltage generator depends upon the system. Figure 23 shows one possible application circuit.
- A low-pass filtered version of the system supply followed by a buffer such as the zero-drift OPA735 can also be used in cases where the system power supply is noisy. Care should be taken to ensure that the voltage at the V_{DD} input does not exceed 7 V (especially during power up) to avoid damage to the converter. This can be done easily using single supply CMOS amplifiers like the OPA735. Figure 24 shows one possible application circuit.

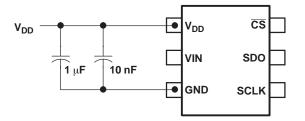
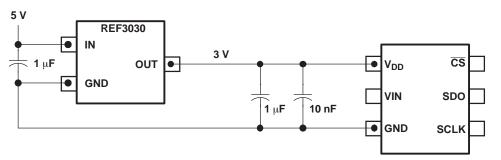


Figure 22. Supply/Reference Decoupling Capacitors







SLAS750A - JUNE 2011 - REVISED JUNE 2011

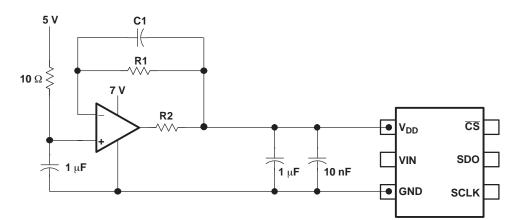


Figure 24. Buffering with the OPA735



11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
ADS7887MDBVT	ACTIVE	SOT-23	DBV	6	250	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-55 to 125	BCNM	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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OTHER QUALIFIED VERSIONS OF ADS7887M :

Catalog: ADS7887



NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE OPTION ADDENDUM

11-Apr-2013

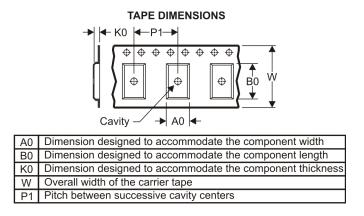
PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal				
Device	Package	Package	Pins	S

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ADS7887MDBVT	SOT-23	DBV	6	250	177.8	9.7	3.2	3.1	1.39	4.0	8.0	Q3

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PACKAGE MATERIALS INFORMATION

22-Jun-2011



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ADS7887MDBVT	SOT-23	DBV	6	250	184.0	184.0	50.0

DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
 - A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
 - È Falls within JEDEC MO-178 Variation AB, except minimum lead width.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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